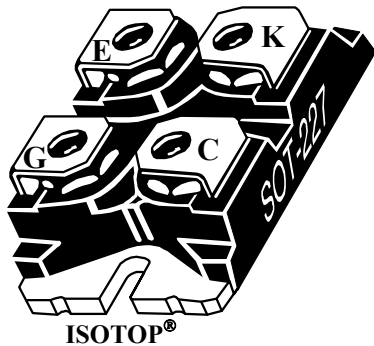
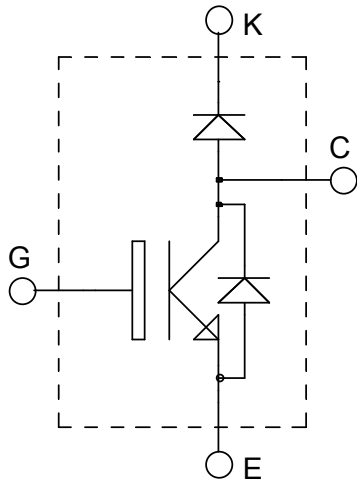


**ISOTOP<sup>®</sup> Boost chopper  
Trench + Field Stop IGBT3**

**$V_{CES} = 1200V$   
 $I_C = 100A @ T_c = 80^{\circ}C$**



### Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction
- Brake switch

### Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- ISOTOP<sup>®</sup> Package (SOT-227)
- Very low stray inductance
- High level of integration

### Benefits

- Low conduction losses
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_C$  of  $V_{CEsat}$
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	1200	V
$I_{C1}$	Continuous Collector Current	$T_C = 25^{\circ}C$	A
$I_{C2}$		$T_C = 80^{\circ}C$	
$I_{CM}$	Pulsed Collector Current	$T_C = 25^{\circ}C$	280
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_C = 25^{\circ}C$	480
$I_{FAV}$	Maximum Average Forward Current	$T_C = 80^{\circ}C$	A
$I_{FRMS}$	RMS Forward Current (Square wave, 50% duty)		
			34

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1200V$			5	mA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 100A$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	1.4 2.0	1.7 2.1	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 4mA$		5.0	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = \pm 20V, V_{CE} = 0V$			400	nA

**Dynamic Characteristics**

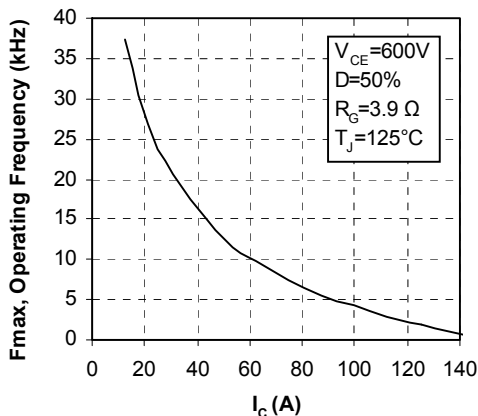
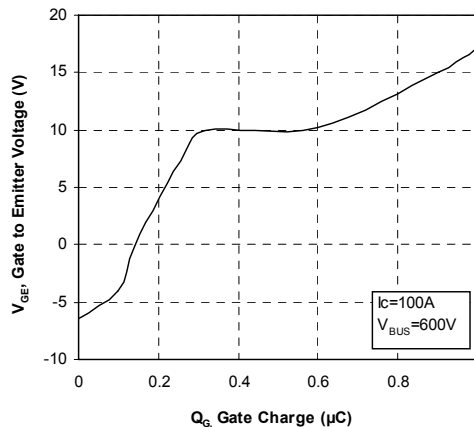
Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V$		7200		pF
$C_{oes}$	Output Capacitance	$V_{CE} = 25V$		400		
$C_{res}$	Reverse Transfer Capacitance	$f = 1MHz$		300		
$Q_G$	Gate charge	$V_{GE} = -8/15V, I_C = 100A$ $V_{CE} = 600V$		0.9		$\mu\text{C}$
$T_{d(on)}$	Turn-on Delay Time	Resistive Switching ( $25^\circ\text{C}$ ) $V_{GE} = 15V$ $V_{Bus} = 600V$ $I_C = 100A$ $R_G = 3.9\Omega$		260		ns
$T_r$	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			420		
$T_f$	Fall Time			70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $125^\circ\text{C}$ ) $V_{GE} = 15V$ $V_{Bus} = 600V$ $I_C = 100A$ $R_G = 3.9\Omega$		290		ns
$T_r$	Rise Time			45		
$T_{d(off)}$	Turn-off Delay Time			520		
$T_f$	Fall Time			90		
$E_{on}$	Turn-on Switching Energy				10	
$E_{off}$	Turn-off Switching Energy			12		

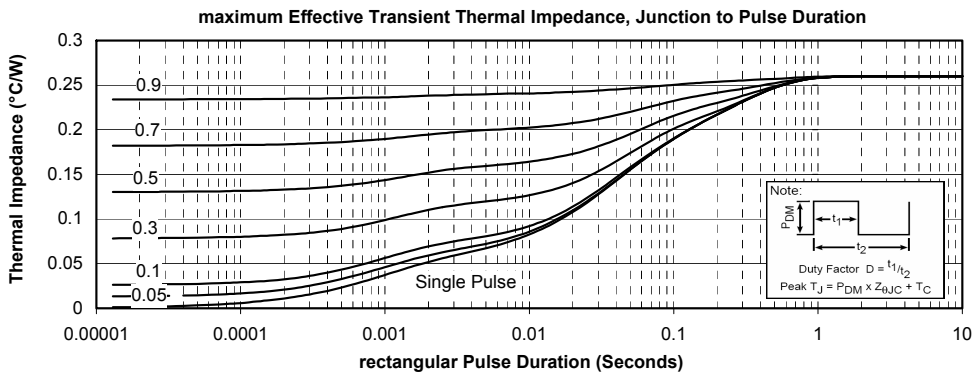
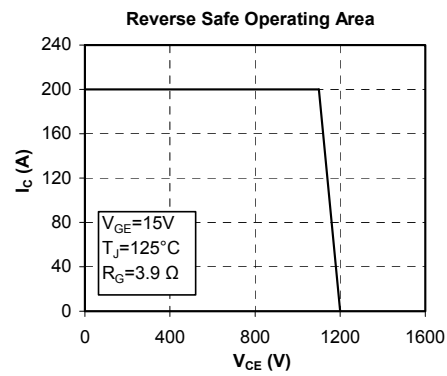
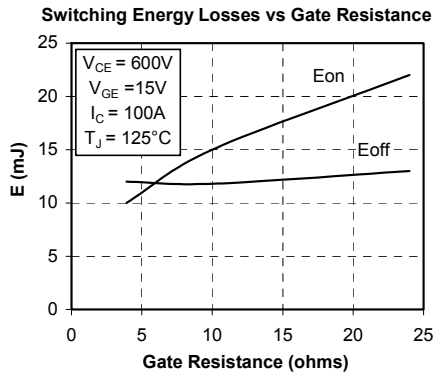
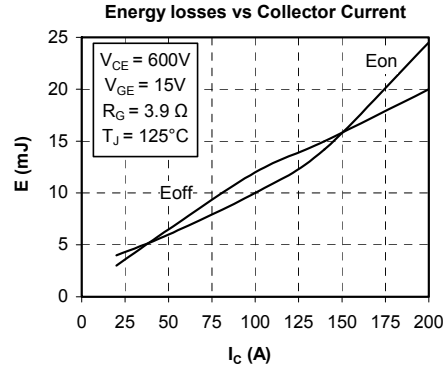
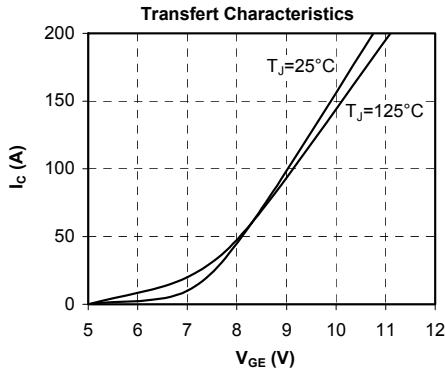
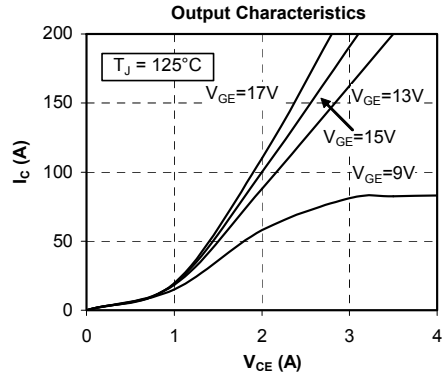
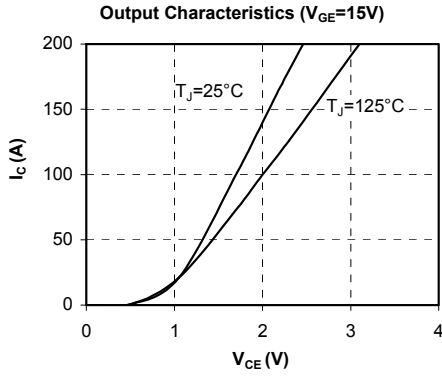
**Chopper diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
V <sub>F</sub>	Diode Forward Voltage	I <sub>F</sub> = 30A		2.0	2.5	V
		I <sub>F</sub> = 60A		2.3		
		I <sub>F</sub> = 30A	T <sub>j</sub> = 125°C	1.8		
I <sub>RM</sub>	Maximum Reverse Leakage Current	V <sub>R</sub> = 1200V	T <sub>j</sub> = 25°C		250	μA
		V <sub>R</sub> = 1200V	T <sub>j</sub> = 125°C		500	
C <sub>T</sub>	Junction Capacitance	V <sub>R</sub> = 200V		32		pF
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 1A, V <sub>R</sub> = 30V di/dt = 100A/μs	T <sub>j</sub> = 25°C		31	ns
	Reverse Recovery Time		T <sub>j</sub> = 25°C		370	
			T <sub>j</sub> = 125°C		500	
I <sub>RRM</sub>	Maximum Reverse Recovery Current	I <sub>F</sub> = 30A V <sub>R</sub> = 800V di/dt = 200A/μs	T <sub>j</sub> = 25°C		5	A
			T <sub>j</sub> = 125°C		12	
			T <sub>j</sub> = 25°C		660	
Q <sub>rr</sub>	Reverse Recovery Charge		T <sub>j</sub> = 25°C		3450	nC
			T <sub>j</sub> = 125°C			
t <sub>rr</sub>	Reverse Recovery Time	I <sub>F</sub> = 30A	T <sub>j</sub> = 125°C		220	ns
Q <sub>rr</sub>	Reverse Recovery Charge	V <sub>R</sub> = 800V			4650	nC
I <sub>RRM</sub>	Maximum Reverse Recovery Current	di/dt = 1000A/μs			37	A

**Thermal and package characteristics**

Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance	IGBT		0.26	°C/W
		Diode		1.1	
R <sub>thJA</sub>	Junction to Ambient (IGBT & Diode)			20	°C/W
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t = 1 min, 50/60Hz	2500			V
T <sub>J</sub> , T <sub>STG</sub>	Storage Temperature Range	-55		150	°C
T <sub>L</sub>	Max Lead Temp for Soldering: 0.063" from case for 10 sec			300	
Torque	Mounting torque (Mounting = 8-32 or 4mm Machine and terminals = 4mm Machine)			1.5	N.m
Wt	Package Weight		29.2		g

**Typical IGBT Performance Curve**
**Operating Frequency vs Collector Current**

**Gate Charge vs Gate to Emitter Voltage**




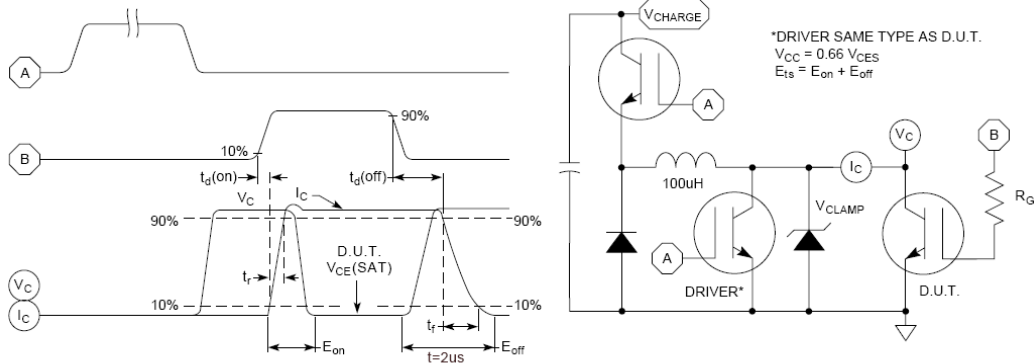


Figure 15, Switching Loss Test Circuit and Waveforms

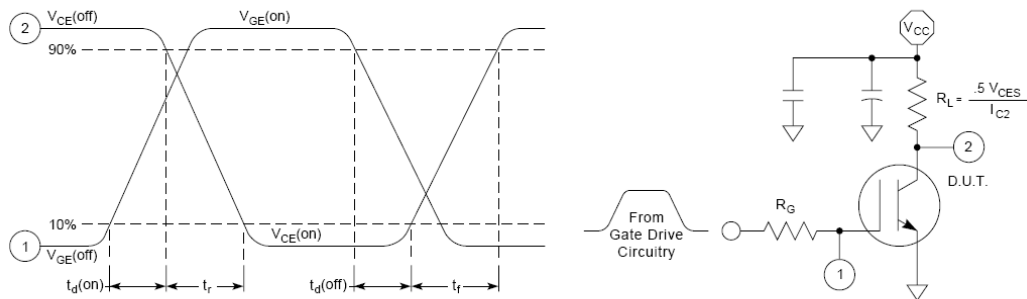
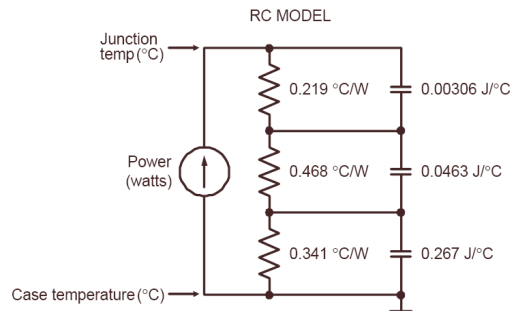
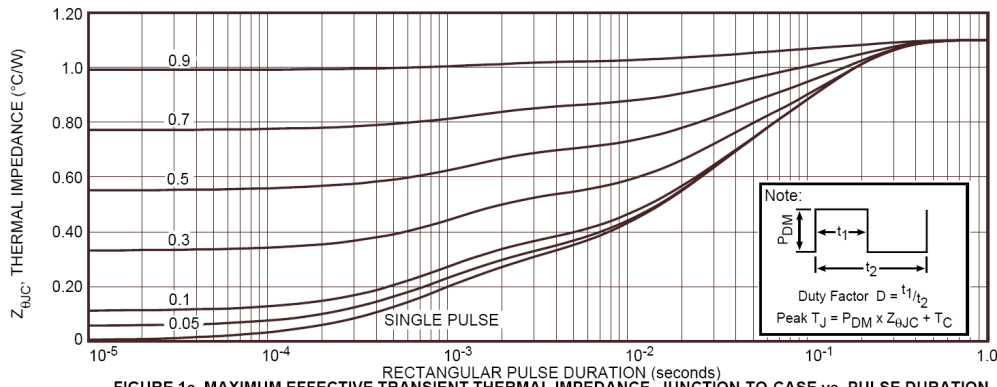


Figure 16, Resistive Switching Time Test Circuit and Waveforms

## Typical Diode Performance Curve



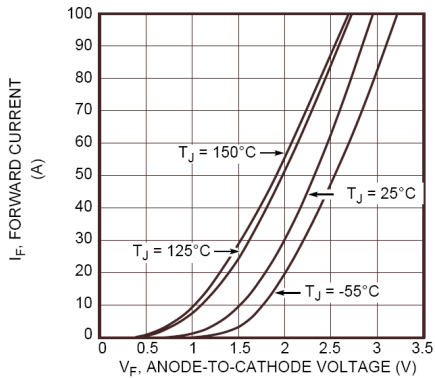


Figure 2. Forward Current vs. Forward Voltage

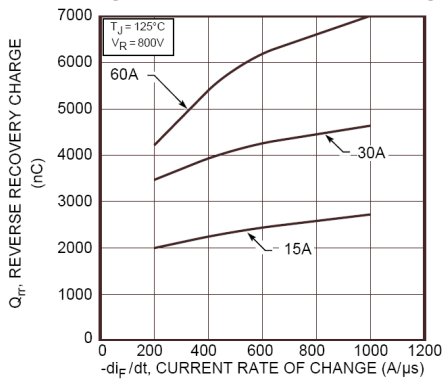


Figure 4. Reverse Recovery Charge vs. Current Rate of Change

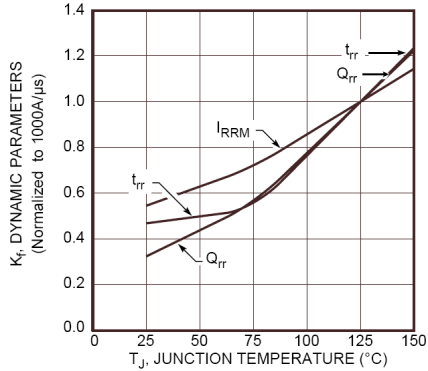


Figure 6. Dynamic Parameters vs. Junction Temperature

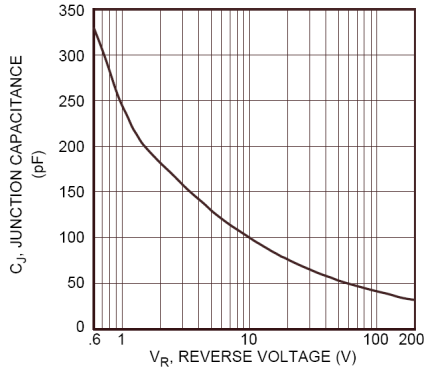


Figure 8. Junction Capacitance vs. Reverse Voltage

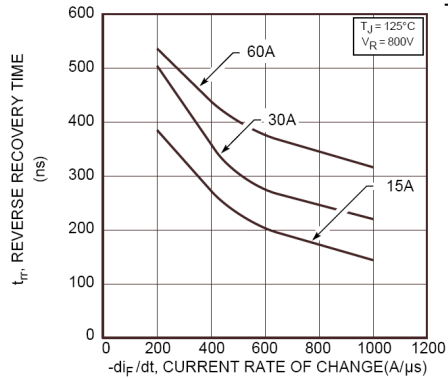


Figure 3. Reverse Recovery Time vs. Current Rate of Change

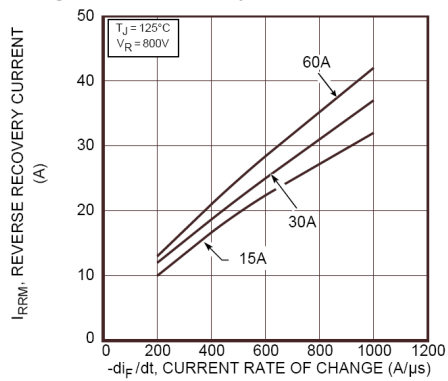


Figure 5. Reverse Recovery Current vs. Current Rate of Change

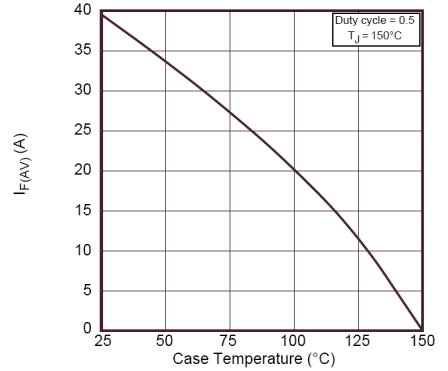


Figure 7. Maximum Average Forward Current vs. Case Temperature

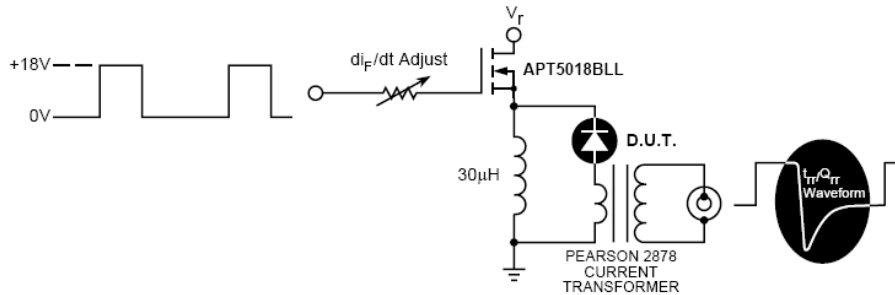


Figure 9. Diode Test Circuit

- 1  $I_F$  - Forward Conduction Current
- 2  $di_F/dt$  - Rate of Diode Current Change Through Zero Crossing.
- 3  $I_{RRM}$  - Maximum Reverse Recovery Current.
- 4  $t_{rr}$  - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through  $I_{RRM}$  and  $0.25 \cdot I_{RRM}$  passes through zero.
- 5  $Q_{rr}$  - Area Under the Curve Defined by  $I_{RRM}$  and  $t_{rr}$ .

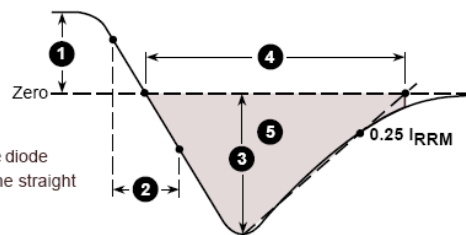
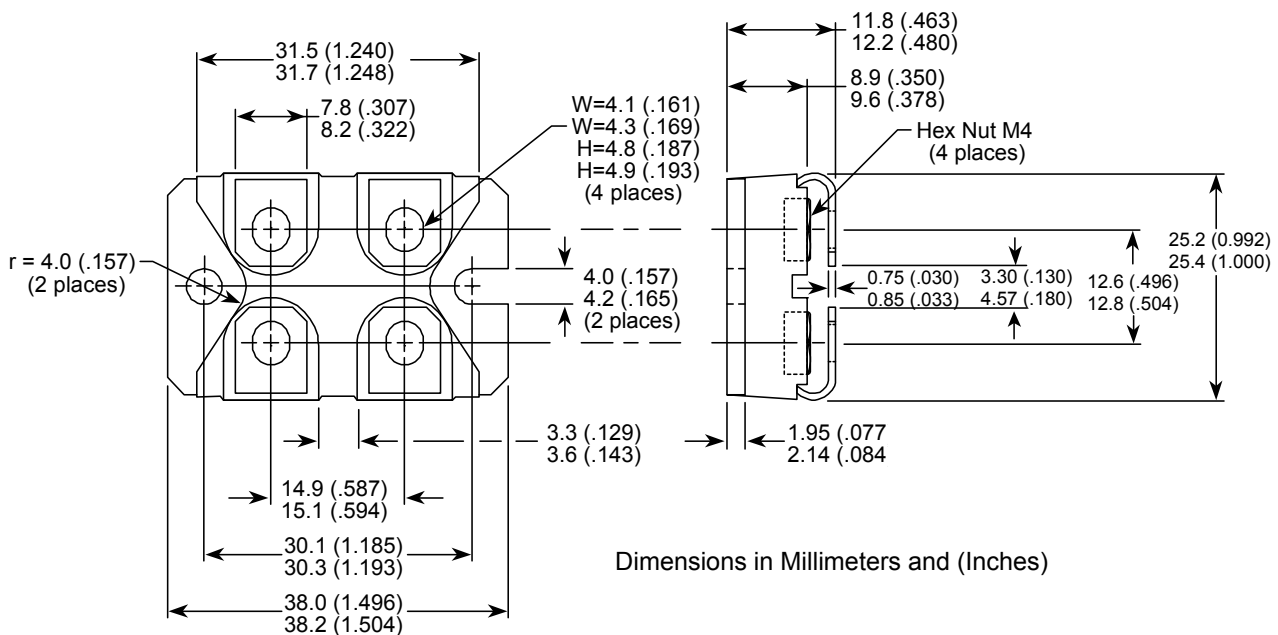


Figure 10. Diode Reverse Recovery Waveform and Definitions

## SOT-227 (ISOTOP<sup>®</sup>) Package Outline



ISOTOP<sup>®</sup> is a registered trademark of ST Microelectronics NV

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